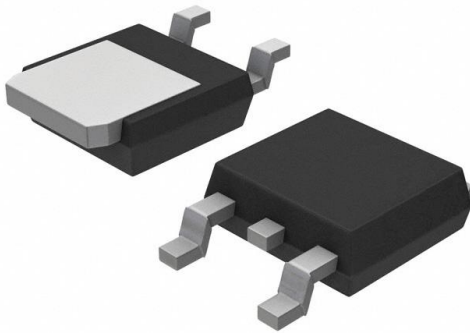


# NJVNJD2873T4G-VF01 Datasheet

[www.digi-electronics.com](http://www.digi-electronics.com)



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	NJVNJD2873T4G-VF01-DG
Manufacturer	<a href="#">onsemi</a>
Manufacturer Product Number	NJVNJD2873T4G-VF01
Description	TRANS NPN 50V 2A DPAK
Detailed Description	Bipolar (BJT) Transistor NPN 50 V 2 A 65MHz 1.68 W Surface Mount DPAK



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

DiGi is a global authorized distributor of electronic components.

## Purchase and inquiry

Manufacturer Product Number:

NJVNJD2873T4G-VF01

Series:

-

Transistor Type:

NPN

Voltage - Collector Emitter Breakdown (Max):

50 V

Current - Collector Cutoff (Max):

100nA (ICBO)

Power - Max:

1.68 W

Operating Temperature:

-65°C ~ 175°C (TJ)

Package / Case:

TO-252-3, DPAK (2 Leads + Tab), SC-63

Base Product Number:

NJVNJD2873

Manufacturer:

onsemi

Product Status:

Obsolete

Current - Collector (Ic) (Max):

2 A

Vce Saturation (Max) @ Ib, Ic:

300mV @ 50mA, 1A

DC Current Gain (hFE) (Min) @ Ic, Vce:

120 @ 500mA, 2V

Frequency - Transition:

65MHz

Mounting Type:

Surface Mount

Supplier Device Package:

DPAK

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0075

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

# NJD2873

## Power Transistors

### NPN Silicon DPAK For Surface Mount Applications

Designed for high-gain audio amplifier applications.

#### Features

- High DC Current Gain
- Low Collector–Emitter Saturation Voltage
- High Current–Gain – Bandwidth Product
- Epoxy Meets UL 94 V–0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Base Voltage	$V_{CB}$	50	Vdc
Collector–Emitter Voltage	$V_{CEO}$	50	Vdc
Emitter–Base Voltage	$V_{EB}$	5	Vdc
Collector Current – Continuous	$I_C$	2	Adc
Collector Current – Peak	$I_{CM}$	3	Adc
Base Current	$I_B$	0.4	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	15 0.1	W W/ $^\circ\text{C}$
Total Device Dissipation @ $T_A = 25^\circ\text{C}^*$ Derate above $25^\circ\text{C}$	$P_D$	1.68 0.011	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	–65 to +175	$^\circ\text{C}$
ESD – Human Body Model	HBM	3B	V
ESD – Machine Model	MM	C	V

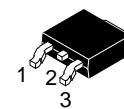
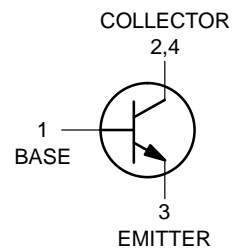
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



**ON Semiconductor®**

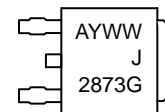
[www.onsemi.com](http://www.onsemi.com)

**SILICON  
POWER TRANSISTORS  
2 AMPERES  
50 VOLTS  
15 WATTS**



**DPAK  
CASE 369C  
STYLE 1**

#### MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb–Free Device

#### ORDERING INFORMATION

Device	Package	Shipping†
NJD2873T4G	DPAK (Pb–Free)	2,500 Units / Reel
NJVNJD2873T4G	DPAK (Pb–Free)	2,500 Units / Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

**NJD2873**

**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction-to-Case Junction-to-Ambient (Note 1)	$R_{\theta JC}$ $R_{\theta JA}$	10 89.3	°C/W

1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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**OFF CHARACTERISTICS**

Collector-Emitter Sustaining Voltage (Note 2) ( $I_C = 10\text{ mAdc}$ , $I_B = 0$ )	$V_{CEO(sus)}$	50	-	Vdc
Collector Cutoff Current ( $V_{CB} = 50\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	-	100	nAdc
Emitter Cutoff Current ( $V_{BE} = 5\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	-	100	nAdc

**ON CHARACTERISTICS**

DC Current Gain (Note 2) ( $I_C = 0.5\text{ A}$ , $V_{CE} = 2\text{ V}$ ) ( $I_C = 2\text{ Adc}$ , $V_{CE} = 2\text{ Vdc}$ ) ( $I_C = 0.75\text{ Adc}$ , $V_{CE} = 1.6\text{ Vdc}$ , $-40^\circ\text{C} \leq T_J \leq 150^\circ\text{C}$ )	$h_{FE}$	120 40 80	360 -	-
Collector-Emitter Saturation Voltage (Note 2) ( $I_C = 1\text{ A}$ , $I_B = 0.05\text{ A}$ )	$V_{CE(sat)}$	-	0.3	Vdc
Base-Emitter Saturation Voltage (Note 2) ( $I_C = 1\text{ A}$ , $I_B = 0.05\text{ Adc}$ )	$V_{BE(sat)}$	-	1.2	Vdc
Base-Emitter On Voltage (Note 2) ( $I_C = 1\text{ Adc}$ , $V_{CE} = 2\text{ Vdc}$ ) ( $I_C = 0.75\text{ Adc}$ , $V_{CE} = 1.6\text{ Vdc}$ , $-40^\circ\text{C} \leq T_J \leq 150^\circ\text{C}$ )	$V_{BE(on)}$	- -	1.2 0.95	Vdc

**DYNAMIC CHARACTERISTICS**

Current-Gain - Bandwidth Product (Note 3) ( $I_C = 100\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f_{test} = 10\text{ MHz}$ )	$f_T$	65	-	MHz
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 0.1\text{ MHz}$ )	$C_{ob}$	-	80	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\approx$  2%.

3.  $f_T = |h_{fe}| \cdot f_{test}$

# NJD2873

## TYPICAL CHARACTERISTICS

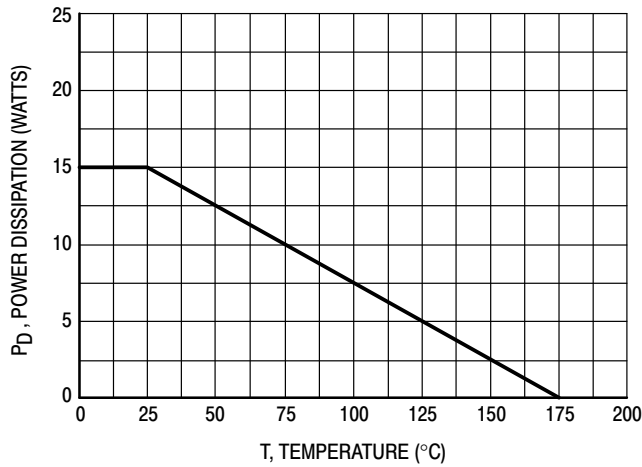


Figure 1. Power Derating

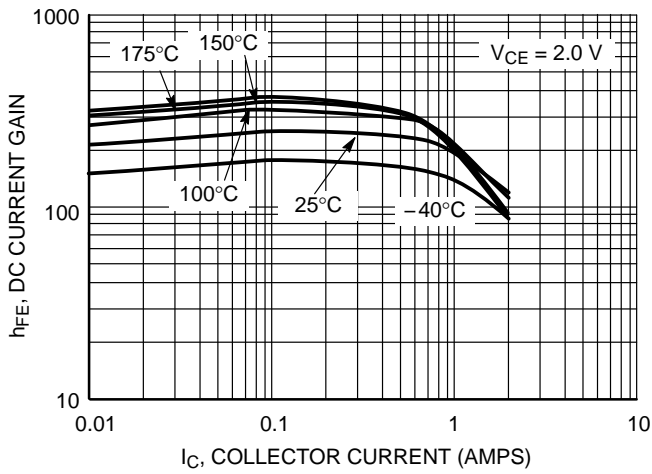


Figure 2. DC Current Gain

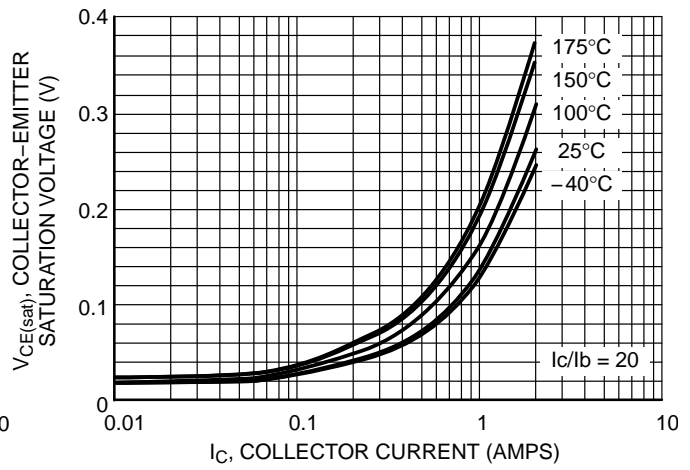


Figure 3. Collector-Emitter Saturation Voltage

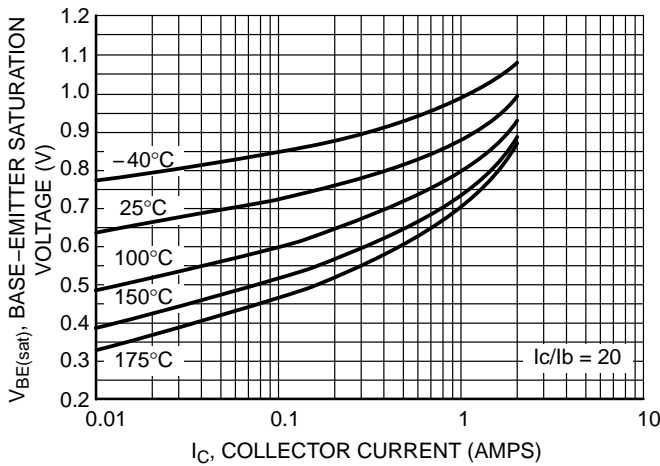


Figure 4. Base-Emitter Saturation Voltage

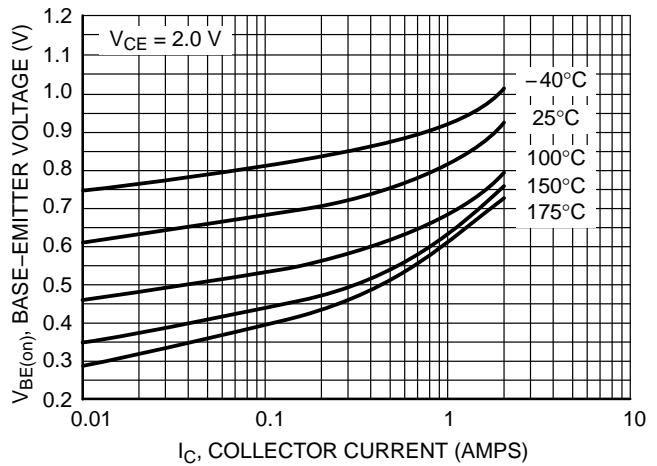
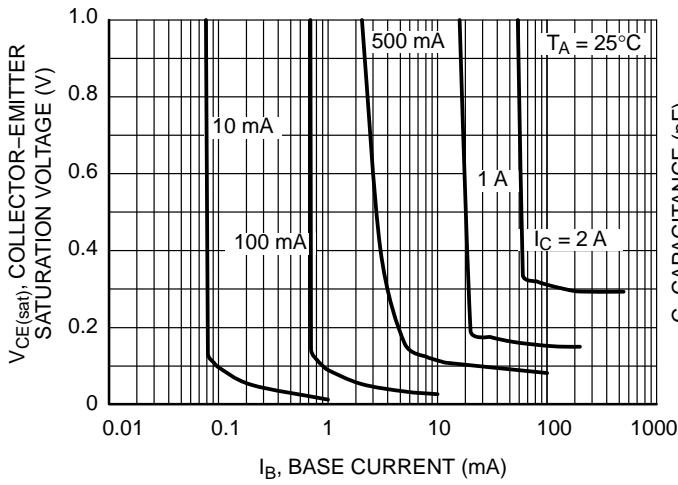
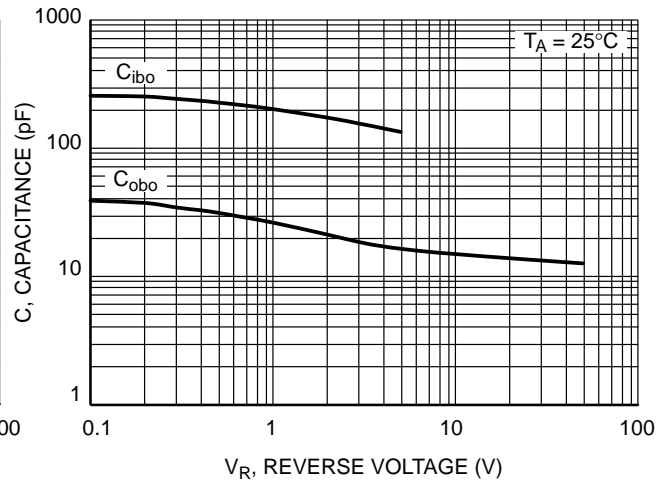


Figure 5. Base-Emitter Voltage

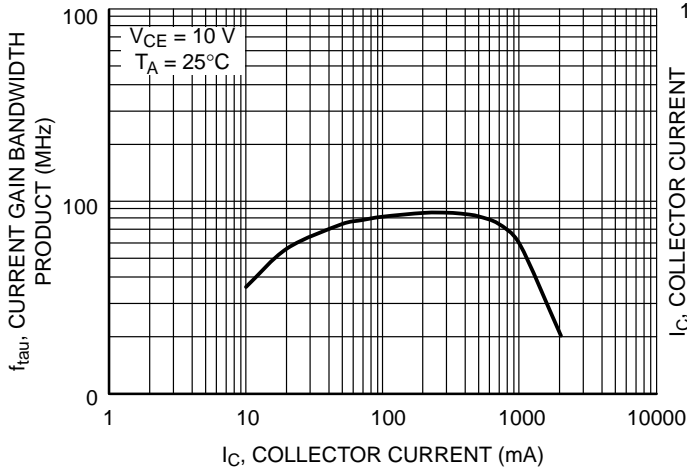
**NJD2873**



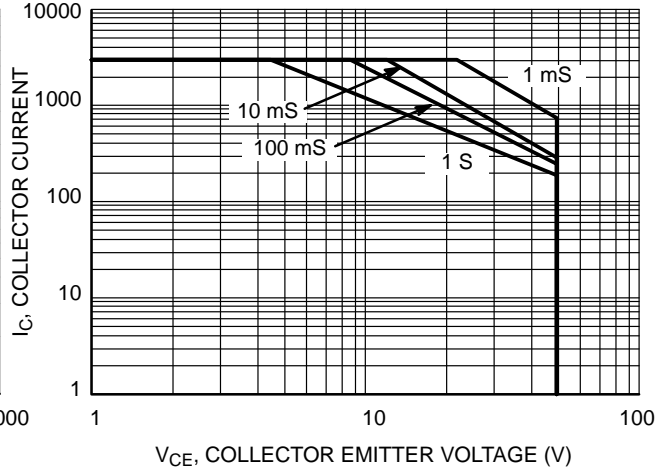
**Figure 6. Saturation Region**



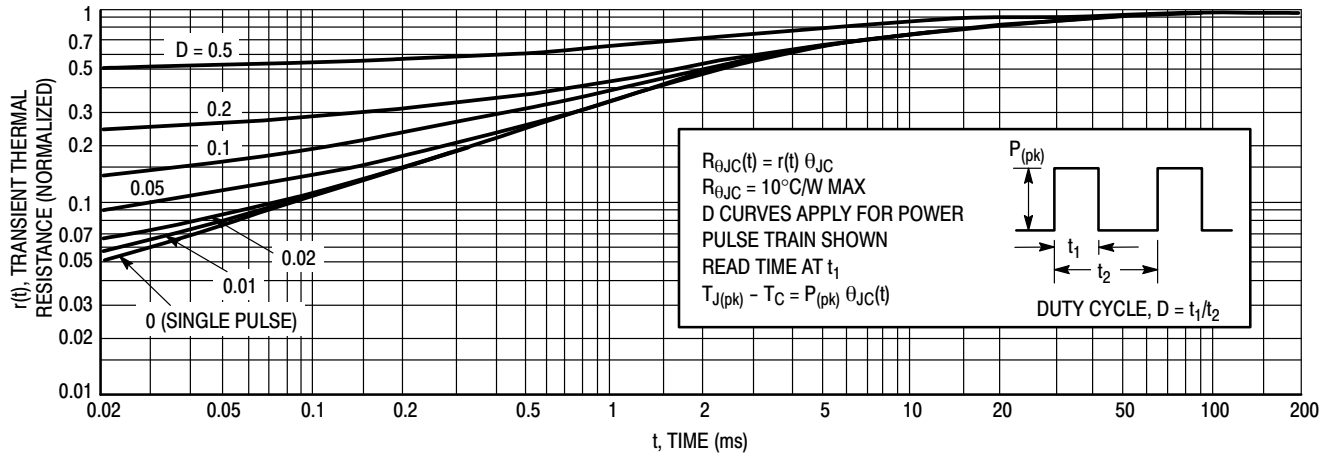
**Figure 7. Capacitance**



**Figure 8. Saturation Region**



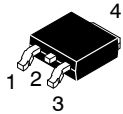
**Figure 9. Capacitance**



**Figure 10. Thermal Response**



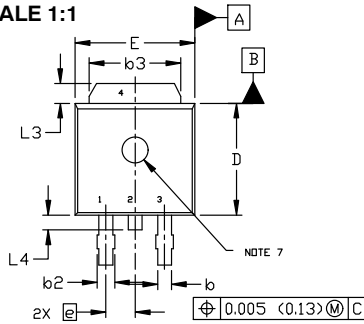
**MECHANICAL CASE OUTLINE  
PACKAGE DIMENSIONS**



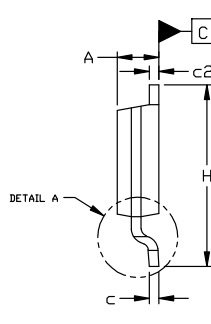
**DPAK (SINGLE GAUGE)  
CASE 369C  
ISSUE G**

DATE 31 MAY 2023

SCALE 1:1



TOP VIEW

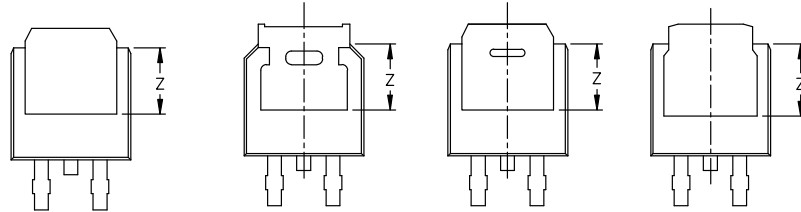


SIDE VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

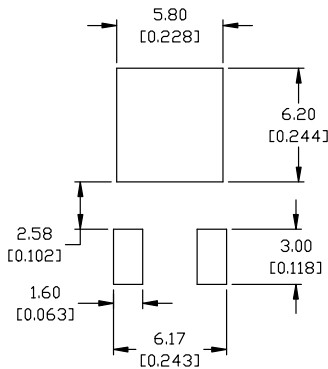
DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---



BOTTOM VIEW

BOTTOM VIEW

ALTERNATE CONSTRUCTIONS

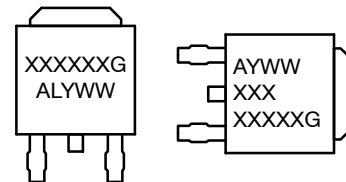


**RECOMMENDED MOUNTING FOOTPRINT\***

\*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

- |  |  |   |   |  |
|--|--|---|---|--|
| <b>STYLE 1:</b><br>PIN 1. BASE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | <b>STYLE 2:</b><br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE<br>4. DRAIN          | <b>STYLE 3:</b><br>PIN 1. ANODE<br>2. CATHODE<br>3. ANODE<br>4. CATHODE | <b>STYLE 4:</b><br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE<br>4. ANODE              | <b>STYLE 5:</b><br>PIN 1. GATE<br>2. ANODE<br>3. CATHODE<br>4. ANODE     |
| <b>STYLE 6:</b><br>PIN 1. MT1<br>2. MT2<br>3. GATE<br>4. MT2                 | <b>STYLE 7:</b><br>PIN 1. GATE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | <b>STYLE 8:</b><br>PIN 1. N/C<br>2. CATHODE<br>3. ANODE<br>4. CATHODE   | <b>STYLE 9:</b><br>PIN 1. ANODE<br>2. CATHODE<br>3. RESISTOR ADJUST<br>4. CATHODE | <b>STYLE 10:</b><br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE<br>4. ANODE |

**GENERIC MARKING DIAGRAM\***



- IC**                      **Discrete**
- XXXXXX = Device Code  
 A = Assembly Location  
 L = Wafer Lot  
 Y = Year  
 WW = Work Week  
 G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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<b>DESCRIPTION:</b>	<b>DPAK (SINGLE GAUGE)</b>	<b>PAGE 1 OF 1</b>

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